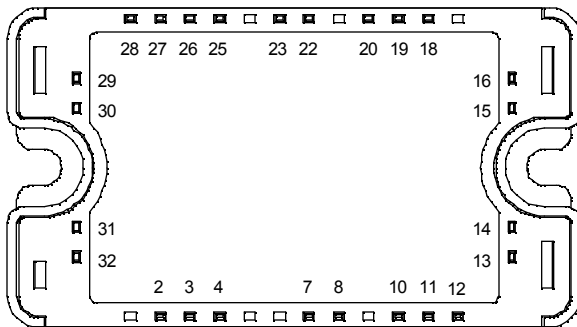
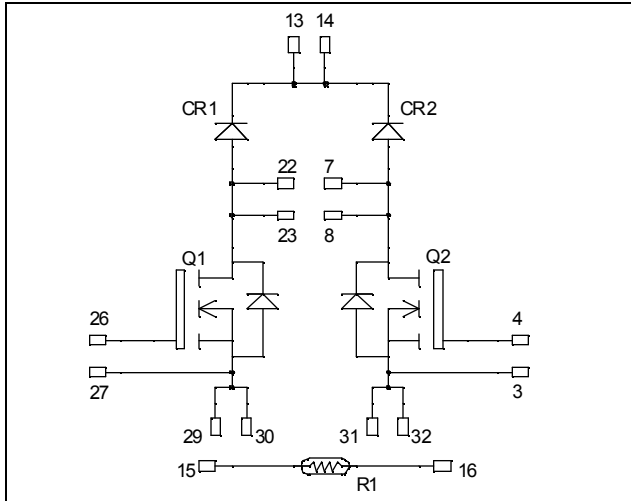


Dual Boost chopper MOSFET Power Module

$V_{DSS} = 1200V$

$R_{DSon} = 570m\Omega$ typ @ $T_j = 25^\circ C$

$I_D = 17A$ @ $T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1200	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	68	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	684	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	22	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1200V$			250	μA
		$V_{GS} = 0V, V_{DS} = 1000V$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 8.5A$		570	684	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5mA$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		5155		pF
C_{oss}	Output Capacitance			770		
C_{rss}	Reverse Transfer Capacitance			130		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 17A$		187		nC
Q_{gs}	Gate – Source Charge			24		
Q_{gd}	Gate – Drain Charge			120		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 800V$ $I_D = 17A$ $R_G = 5\Omega$		20		ns
T_r	Rise Time			15		
$T_{d(off)}$	Turn-off Delay Time			160		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 17A, R_G = 5\Omega$		990		μJ
E_{off}	Turn-off Switching Energy			685		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 17A, R_G = 5\Omega$		1565		μJ
E_{off}	Turn-off Switching Energy			857		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$		250	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		25		A
V_F	Diode Forward Voltage	$I_F = 25A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$	2.1		V
			$T_j = 125^\circ\text{C}$	1.9		
t_{rr}	Reverse Recovery Time	$I_F = 25A$ $V_R = 600V$ $di/dt = 1000A/\mu s$	$T_j = 25^\circ\text{C}$	95		ns
			$T_j = 125^\circ\text{C}$	190		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	2.3		μC
			$T_j = 125^\circ\text{C}$	4.5		

Thermal and package characteristics

Symbol	Characteristic				Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance			Transistor			0.32	°C/W	
				Diode			1.2		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz				2500			V	
T _J	Operating junction temperature range				-40		150	°C	
T _{STG}	Storage Temperature Range				-40		125		
T _C	Operating Case Temperature				-40		100		
Torque	Mounting torque		To heatsink	M4	2.5		4.7	N.m	
Wt	Package Weight							110	g

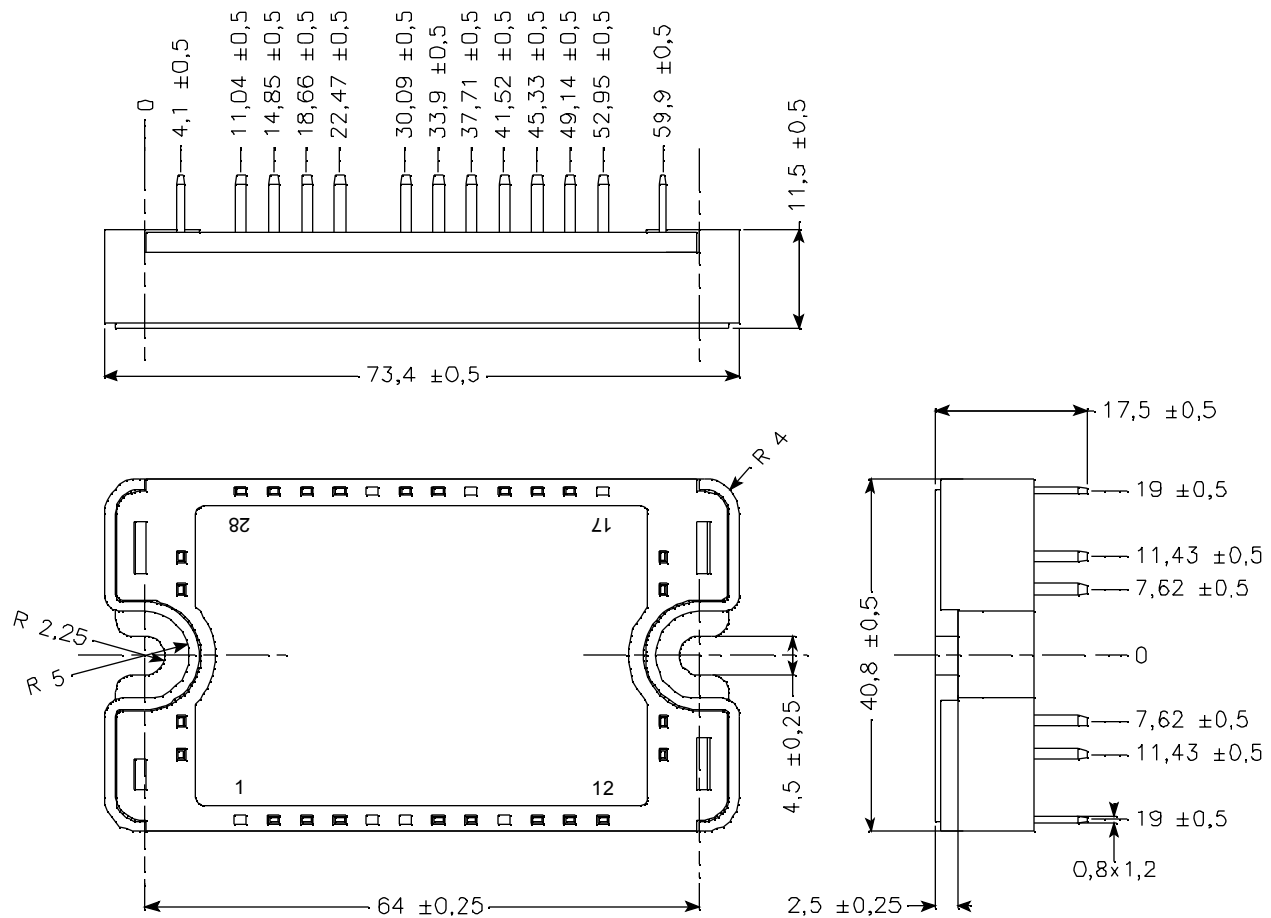
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

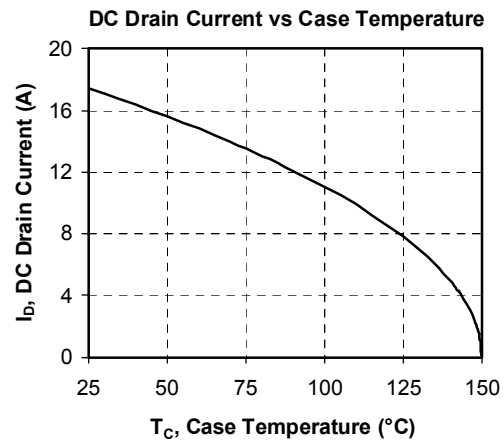
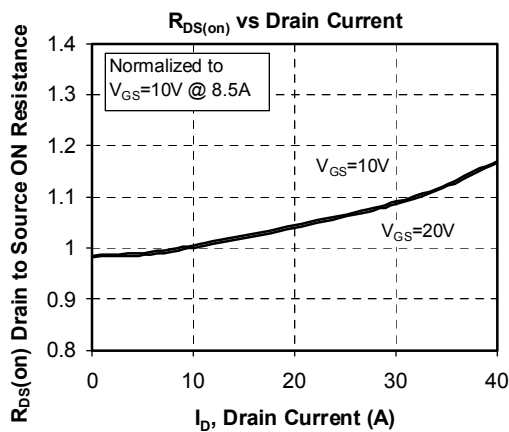
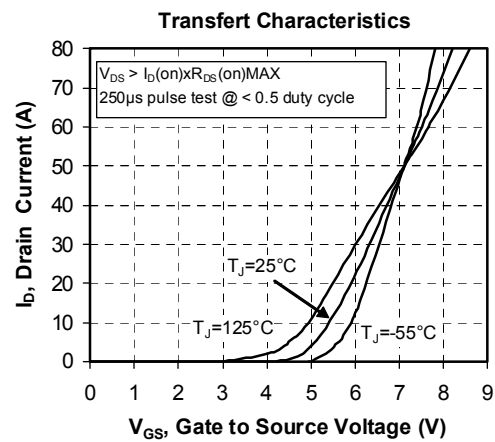
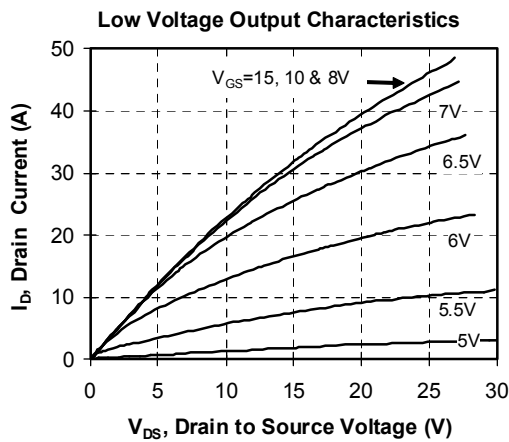
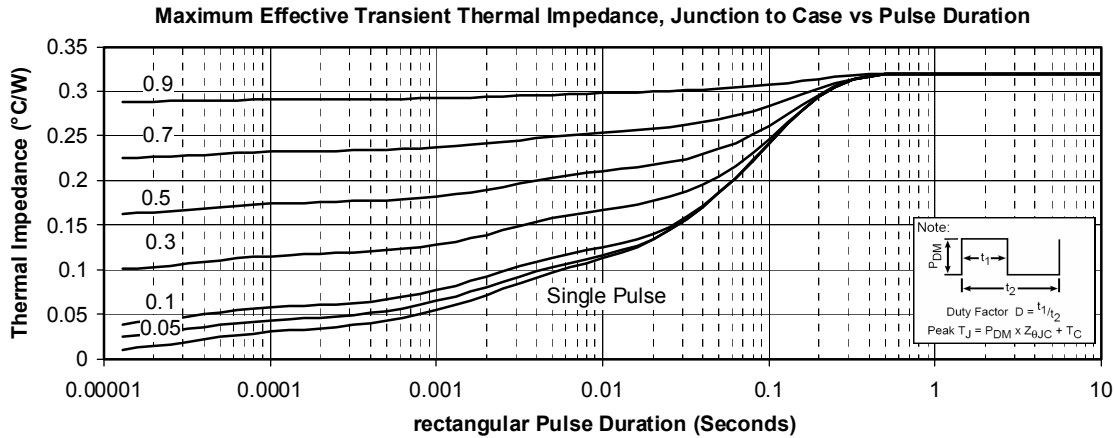
T: Thermistor temperature
R_T: Thermistor value at T

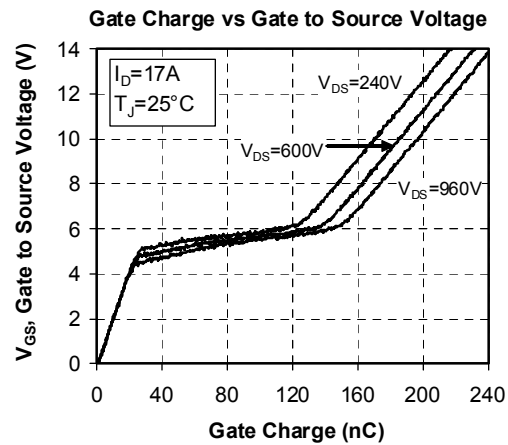
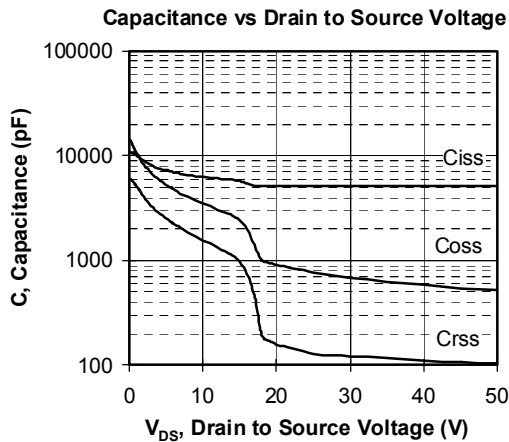
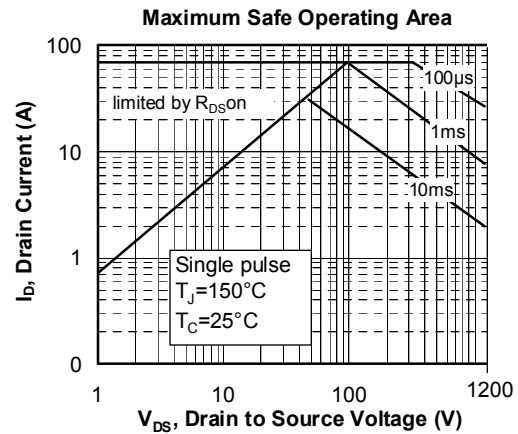
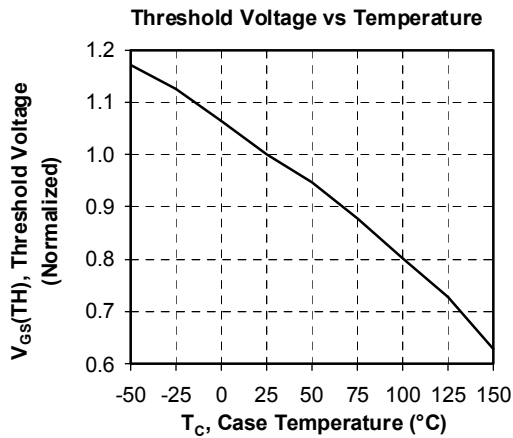
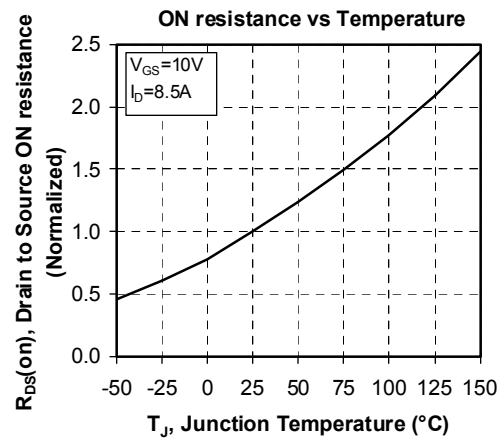
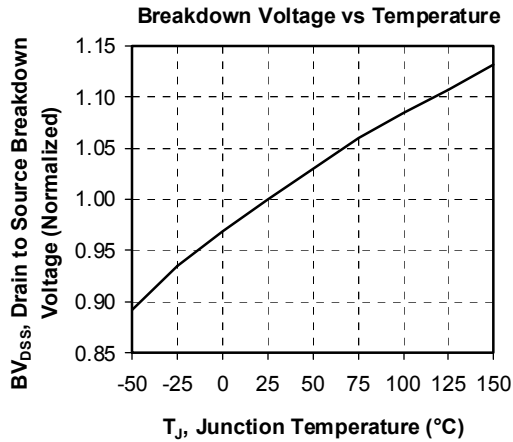
SP3 Package outline (dimensions in mm)

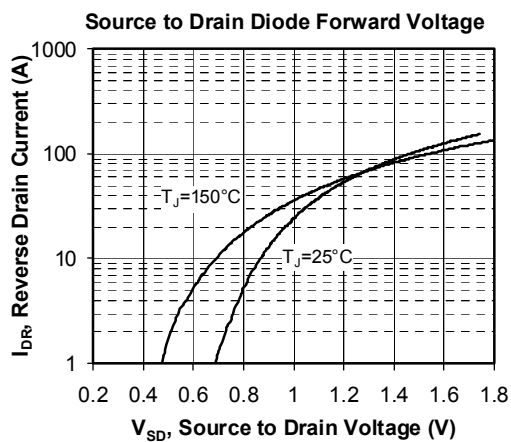
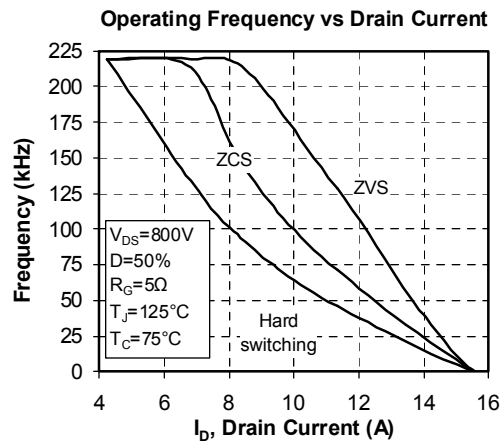
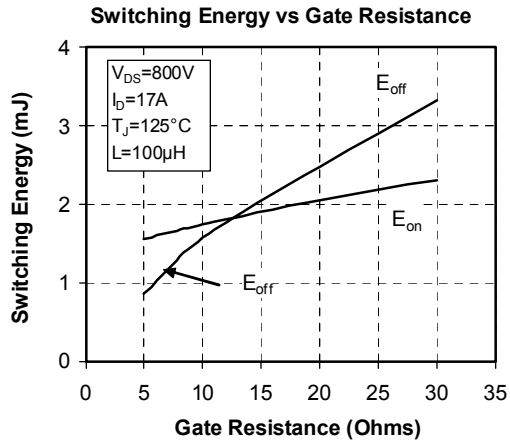
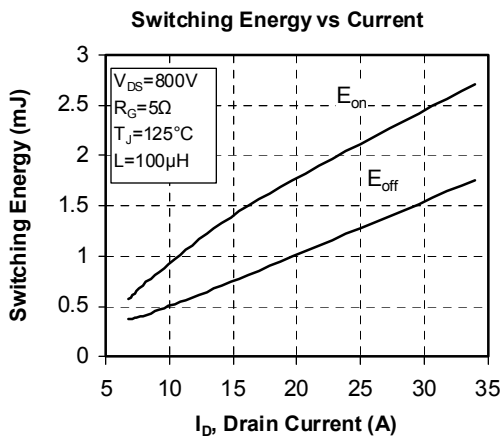
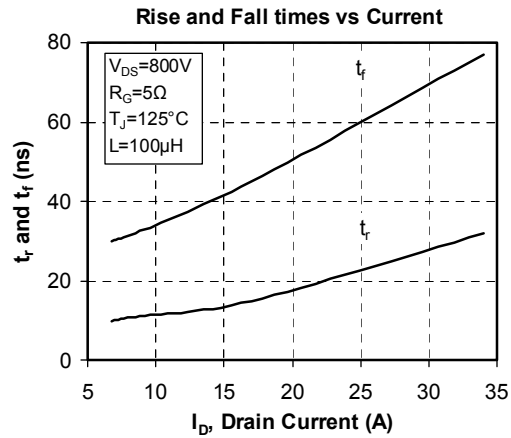
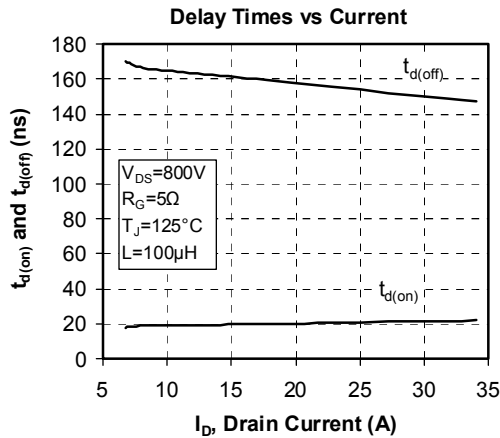


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve







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